

TECHNICAL DATA, PROVISIONAL DATA ONLY  
DATA SHEET 4130, Rev. B

## HERMETIC SILICON CARBIDE RECTIFIER

**DESCRIPTION:** A 1200-VOLT, 10 AMP POWER SILICON CARBIDE RECTIFIER IN A CERAMIC HERMETIC SHD-3 HIGH PROFILE PACKAGE

**FEATURES:**

- NO RECOVERY TIME OR REVERSE RECOVERY LOSSES
- NO TEMPERATURE INFLUENCE ON SWITCHING BEHAVIOR

**MAXIMUM RATINGS**

ALL RATINGS ARE @  $T_C = 25\text{ }^\circ\text{C}$  UNLESS OTHERWISE SPECIFIED.

| RATING   | SYMBOL               | MAX.        | UNITS              |
|--|----------------------|-------------|--------------------|
| PEAK INVERSE VOLTAGE   | PIV                  | 1200        | Volts              |
| MAXIMUM DC OUTPUT CURRENT  | $I_O$                | 10          | Amps               |
| MAXIMUM REPETITIVE FORWARD SURGE CURRENT<br>( $t = 8.3\text{ms}$ , Sine)       | $I_{FRM}$            | 50          | Amps               |
| MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT<br>( $t = 10\mu\text{s}$ , pulse) | $I_{FSM}$            | 150         | Amps               |
| MAXIMUM JUNCTION CAPACITANCE ( $V_r = 5\text{V}$ )                             | $C_T$                | 500         | pF                 |
| MAXIMUM POWER DISSIPATION  | $P_d$                | 30          | W                  |
| MAXIMUM THERMAL RESISTANCE (Junction to Case)                                  | $R_{\theta JC}$      | 1.20        | $^\circ\text{C/W}$ |
| MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE                                | $T_{op}$ , $T_{stg}$ | -55 to +200 | $^\circ\text{C}$   |

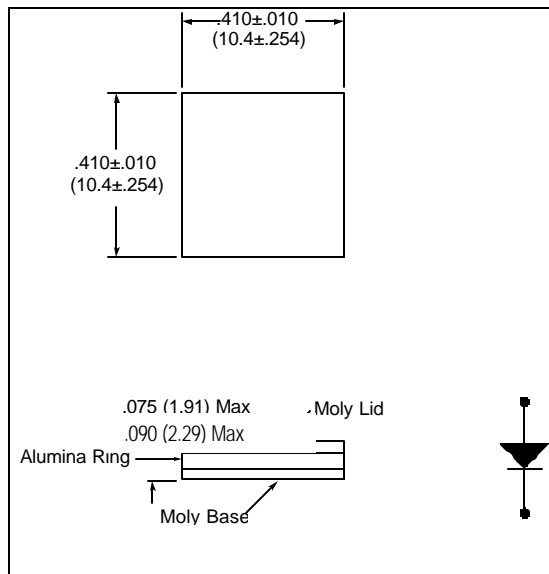
**ELECTRICAL CHARACTERISTICS**

| CHARACTERISTIC   | TYP          | MAX.         | UNITS |
|--|--------------|--------------|-------|
| MAXIMUM FORWARD VOLTAGE DROP $I_f = 10\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$<br>$T_J = 175\text{ }^\circ\text{C}$                             | 1.65<br>2.55 | 1.80<br>3.00 | Volts |
| MAXIMUM REVERSE CURRENT $PIV = 1200\text{V}$ , $T_J = 25\text{ }^\circ\text{C}$<br>$T_J = 175\text{ }^\circ\text{C}$                                 | 0.10<br>0.20 | 0.80<br>4.00 | mA    |
| TOTAL CAPACITIVE CHARGE ( $V_R = 1200\text{V}$ , $I_F = 10\text{A}$ , $di/dt = 500\text{A}/\mu\text{s}$ and $T_J = 25\text{ }^\circ\text{C}$ ) $Q_C$ | 30           | N/A          | nC    |

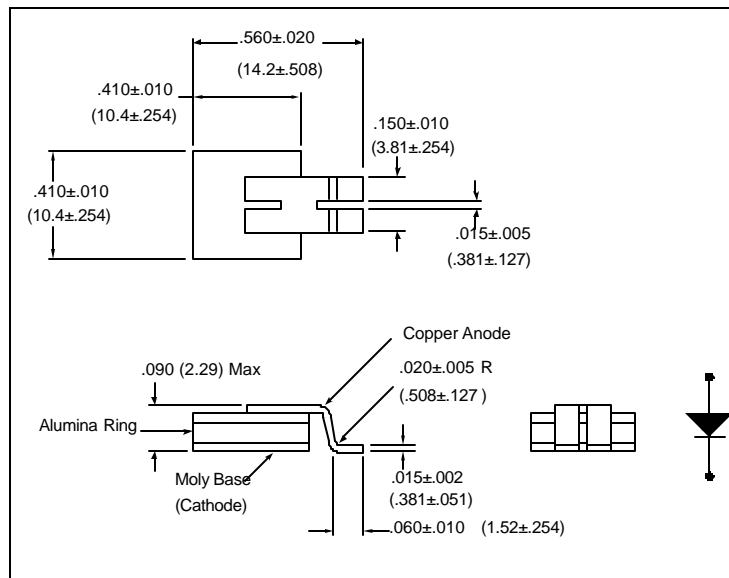
**TECHNICAL DATA, PROVISIONAL DATA ONLY**  
**DATA SHEET 4130, Rev. B**

MECHANICAL DIMENSIONS: In Inches / mm

**SHD-3 (High Profile)**



**SHD-3B (High Profile)**



Application Note: Customers should be aware that at the current stage of technical development of SiC, the reverse avalanche capabilities of the device are limited.

Customer designs will need to accommodate these limitations and avoid exposure of the device to this and other potentially damaging conditions in their applications.

**TECHNICAL DATA**

**DISCLAIMER:**

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.